

INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

BD933/935/937/939/941

DESCRIPTION

- DC Current Gain-
- : h_{FE}= 40(Min)@ I_C= 150mA
- Complement to Type BD934/936/938/940/942
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

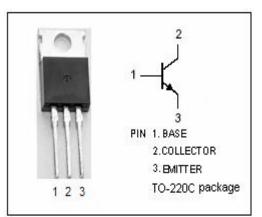
• Designed for use in output stages of audio and television amplifier circuits where high peak powers can occur.

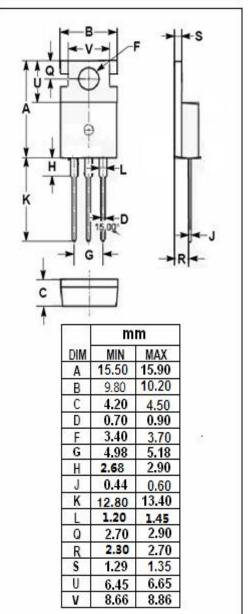
ABSOLUTE MAXIMUM RATINGS(Ta=25C)								
SYMBOL	PARAMETER	VALUE	UNIT					
V _{CBO}		BD933	45					
		BD935	60					
	Collector-Base Voltage	BD937	100	V				
		BD939	120					
		BD941	140					
Vceo		BD933	45	V				
	Collector-Emitter Voltage	BD935	60					
		BD937	80					
		BD939	100					
		BD941	120					
VEBO	Emitter-Base Voltage	5	V					
Ic	Collector Current-Continuous		3	А				
I _{CM}	Collector Current-Peak		7	А				
IB	Base Current-Continuous		0.5	А				
Pc	Collector Power Dissipation @ T _C =25°C		30	W				
TJ	Junction Temperature	150	°C					
T _{stg}	Storage Temperature Ran	-65~150	°C					

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	4.17	°C/W
R _{th j-a}	Rth j-a Thermal Resistance, Junction to Ambient		°C /W





isc website: www.iscsemi.com

¹ *isc & iscsemi* is registered trademark



INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

BD933/935/937/939/941

ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	BD933		45			
		BD935	I _C = 30mA ; I _B = 0	60			
		BD937		80			V
		BD939		100			
		BD941		120			
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage		Ic= 1A; I _B = 0.1A			0.6	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage		I _C = 1A; V _{CE} = 2V			1.3	V
I _{CBO}	Collector Cutoff Current		V _{CB} = V _{CBOmax} ; I _E = 0 V _{CB} = V _{CBOmax} ; I _E = 0,T _J =150℃			0.05 1	mA
I _{CEO}	Collector Cutoff Current		V _{CE} = V _{CEOmax} ; I _B = 0			0.1	mA
I _{EBO}	Emitter Cutoff Current		V _{EB} = 5V; I _C = 0			0.2	mA
$h_{\text{FE-1}}$	DC Current Gain		I _C = 150mA ; V _{CE} = 2V	40		250	
h _{FE-2}	DC Current Gain		I _C = 1A ; V _{CE} = 2V	25			

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.